



勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
 Http://www.100y.com.tw

STPS20120D

POWER SCHOTTKY RECTIFIER

Table 1: Main Product Characteristics

$I_{F(AV)}$	20 A
V_{RRM}	120 V
T_j (max)	175°C
V_F (typ)	0.54 V

FEATURES AND BENEFITS

- High junction temperature capability
- Avalanche rated
- Low leakage current
- Good trade-off between leakage current and forward voltage drop

DESCRIPTION

Single Schottky rectifier suited for high frequency Switch Mode Power Supply.
 Packaged in TO-220AC, this device is intended to be used in notebook & LCD adaptors, desktop SMPS, providing in these applications a margin between the remaining voltages applied on the diode and the voltage capability of the diode.

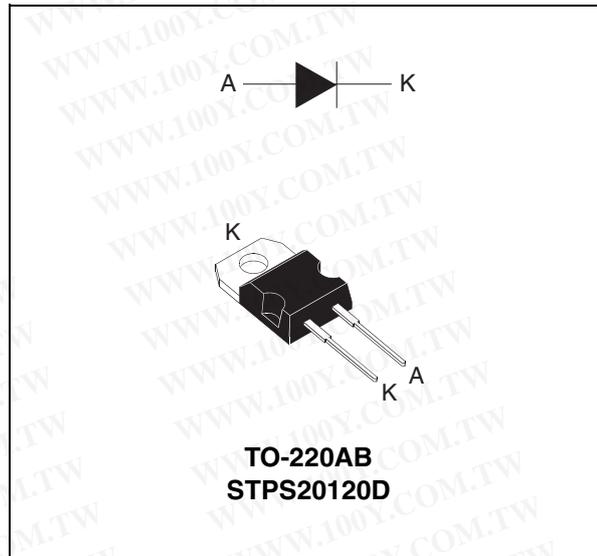


Table 2: Order Code

Part Number	Marking
STPS20120D	STPS20120D

Table 3: Absolute Ratings (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	120	V
$I_{F(RMS)}$	RMS forward voltage	30	A
$I_{F(AV)}$	Average forward current	$\delta = 0.5 \quad T_c = 130^\circ\text{C}$	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ms sinusoidal}$	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1\mu\text{s} \quad T_j = 25^\circ\text{C}$	W
T_{stg}	Storage temperature range	-65 to + 175	°C
T_j	Maximum operating junction temperature *	175	°C

* : $\frac{dP_{tot}}{dT_j} > \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

Table 4: Thermal Parameters

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.2	°C/W

Table 5: Static Electrical Characteristics

Symbol	Parameter	Tests conditions		Min.	Typ	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			20	μA
		$T_j = 125^\circ\text{C}$			3	10	mA
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 5\text{A}$			0.7	V
		$T_j = 125^\circ\text{C}$			0.54	0.58	
		$T_j = 25^\circ\text{C}$	$I_F = 10\text{A}$			0.8	
		$T_j = 125^\circ\text{C}$			0.62	0.66	
		$T_j = 25^\circ\text{C}$	$I_F = 20\text{A}$			0.93	
		$T_j = 125^\circ\text{C}$			0.72	0.76	

Pulse test: * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation: $P = 0.56 \times I_{F(AV)} + 0.010 I_F^2 (RMS)$

Figure 1: Average forward power dissipation versus average forward current

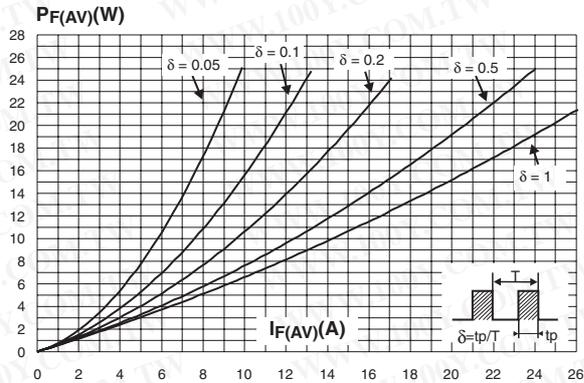


Figure 2: Average forward current versus ambient temperature ($\delta = 0.5$)

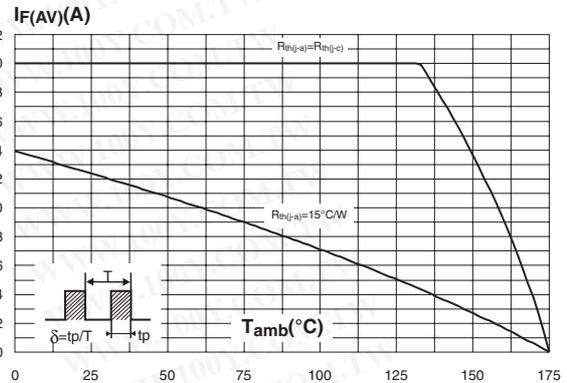


Figure 3: Normalized avalanche power derating versus pulse duration

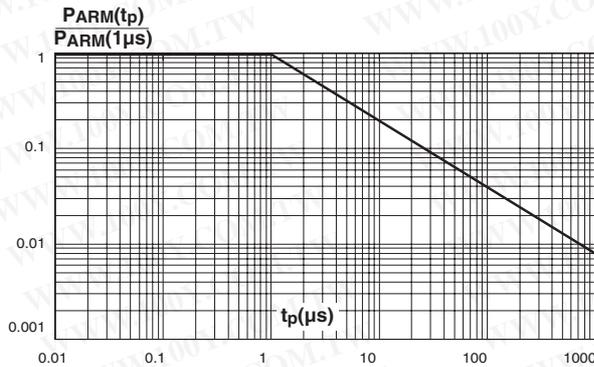


Figure 4: Normalized avalanche power derating versus junction temperature

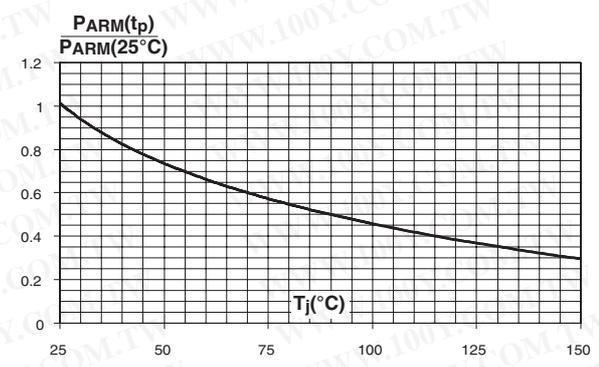


Figure 5: Non repetitive surge peak forward current versus overload duration (maximum values)

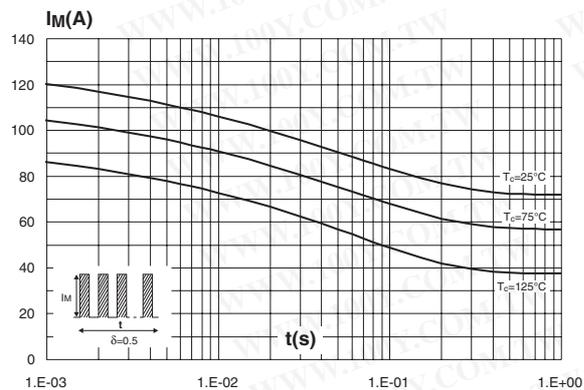


Figure 6: Relative variation of thermal impedance junction to ambient versus pulse duration

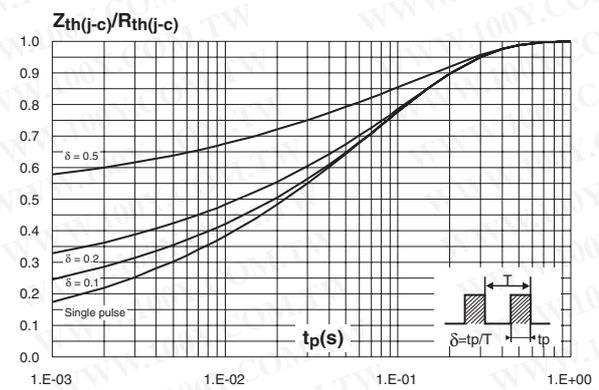


Figure 7: Reverse leakage current versus reverse voltage applied (typical values)

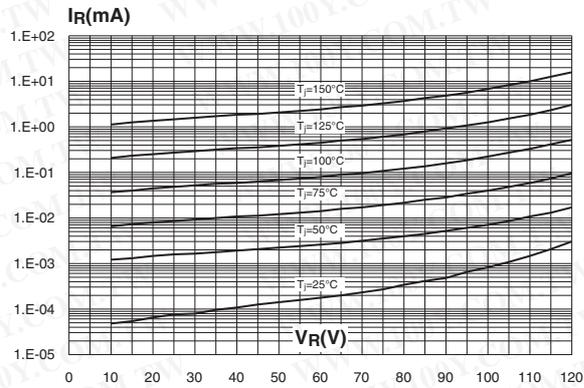


Figure 8: Junction capacitance versus reverse voltage applied (typical values)

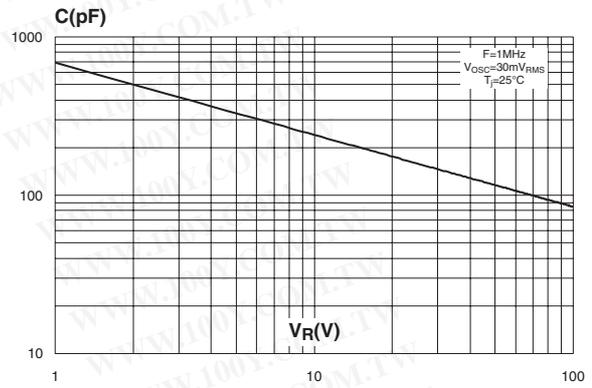
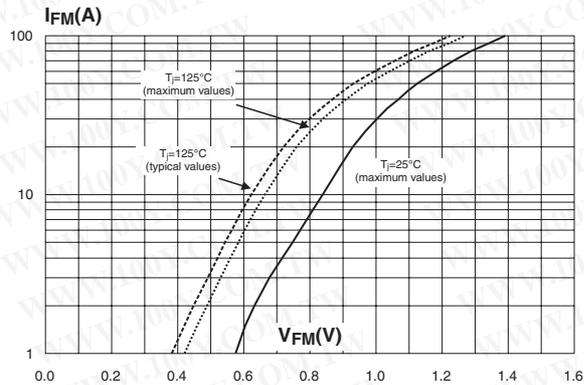


Figure 9: Forward voltage drop versus forward current



勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Figure 10: TO-220AC Package Mechanical Data

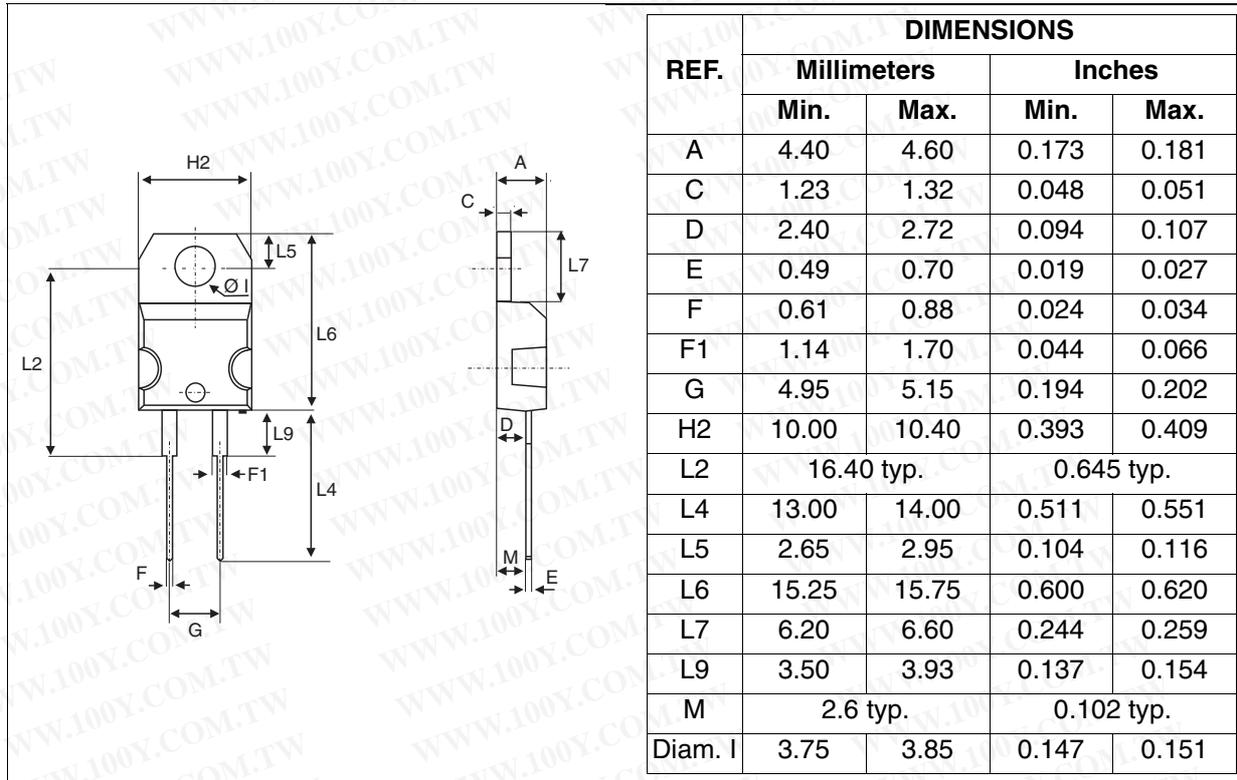


Table 6: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20120D	STPS20120D	TO-220AC	1.90 g	50	Tube

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 m.N.
- Maximum torque value: 0.70 m.N.

Table 7: Revision History

Date	Revision	Description of Changes
18-Feb-2005	1	First issue.

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.
All other names are the property of their respective owners

© 2005 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America
www.st.com

